

FEATURES

- High Voltage Operation : $V_{DS}=50V$
- High Power : 200W (min.) @ $P_{in}=15.8W$ (42dBm)
- High Efficiency: 53%(typ.) @ $P_{in}=15.8W$ (42dBm)

DESCRIPTION

Sumitomo GaN-HEMT EGN28B100IV-R offers high power, high efficiency, ease of matching and greater consistency covering 2.7 to 3.1GHz for S-band radar applications with 50V operation. The low thermal resistance allows to use long pulse up to 5 msec pulse width with duty of 10%.



ABSOLUTE MAXIMUM RATINGS

Item	Symbol	Condition	Rating	Unit
Operating Voltage	V_{DS}		50	V
Drain-Source Voltage	V_{DS}	$V_{GS}=-5V$	120	V
Gate-Source Voltage	V_{GS}		- 5	V
Storage Temperature	T_{stg}		-65 to +100	°C
Channel Temperature	T_{ch}		250	°C

RECOMMENDED OPERATING CONDITION(Case Temperature $T_c=25^{\circ}C$)

Item	Symbol	Condition	Limit	Unit
DC Input Voltage	V_{DS}		≤ 50	V
Forward Gate Current	I_{GF}	RG=6.2 W	≤ 100	mA
Reverse Gate Current	I_{GR}	RG=6.2 W	≥ -14.4	mA
Pulse Width	PW	Duty 10%	≤ 5000	μsec
		Duty 25%	≤ 1500	μsec
Peak Channel Temperature	$T_{ch-peak}$	Duty 10%	≤ 215	°C
		Duty 25%	≤ 205	°C

ELECTRICAL CHARACTERISTICS (Case Temperature $T_c=25^{\circ}C$)

Item	Symbol	Condition	Limit			Unit
			Min.	Typ.	Max.	
Pinch-Off Voltage	V_p	$V_{DS}=50V$ $I_{DS}=72mA$	-1.0	-2.0	-3.5	V
Output Power	P_{out}	$V_{DS}=50V$	200	-	-	W
Drain Efficiency	η_d	$I_{DS(DC)}=1000mA$	-	53	-	%
Power Gain	G_p	$P_{in}=15.8W$ (42dBm)	11.0	-	-	dB
Gain Flatness	GF	f=2.7, 2.9, 3.1GHz PW=200 μsec , Duty 10%	-	0.5	1.0	dB
Thermal Resistance	R_{th}	Channel to Case Measured w/CW at 90W P_{DC}	-	0.56	0.7	°C/W



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THERMAL CHARACTERISTICS IN PULSED RF OPERATION

Transient Thermal Resistance, Channel to Case,	Typ.	Unit
Case Temperature 75°C, Pulse Width 200μsec , Duty 10%	0.15	°C/W
Case Temperature 75°C, Pulse Width 5000μsec , Duty 10%	0.37	°C/W
Case Temperature 75°C, Pulse Width 1500μsec , Duty 25%	0.34	°C/W

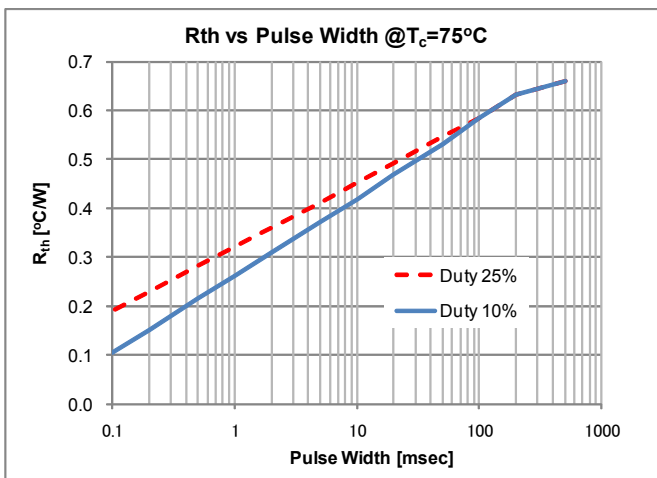
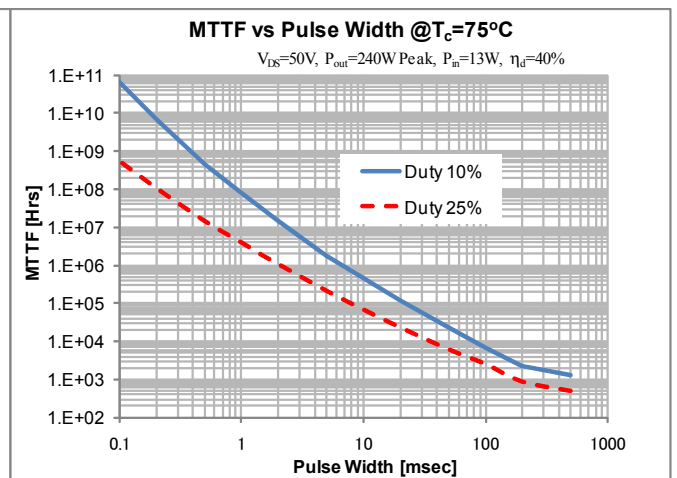


Figure 1. Transient Thermal Resistance vs Pulse Width @T_c = 75°C



V_{DS}=50V, P_{out}=240W peak, P_{in}=12.6W, η_d=40%, T_c=75°C

Figure 2. MTTF vs Pulse Width @T_c = 75°C

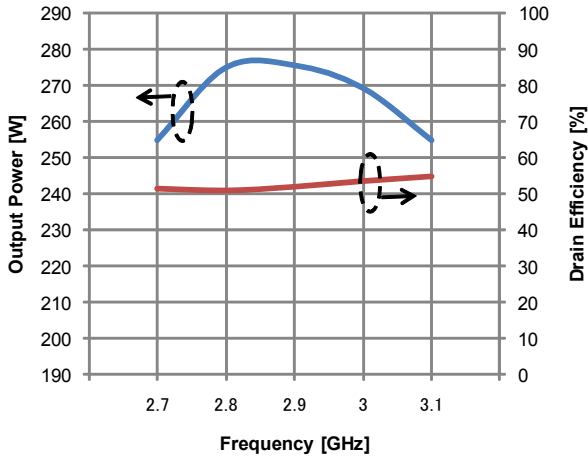
ESD characteristic

Test Methodology	Class
Human Body Model (per JESD22-A114)	1C
Machine Model (per JEIA/ESD22-A115)	C



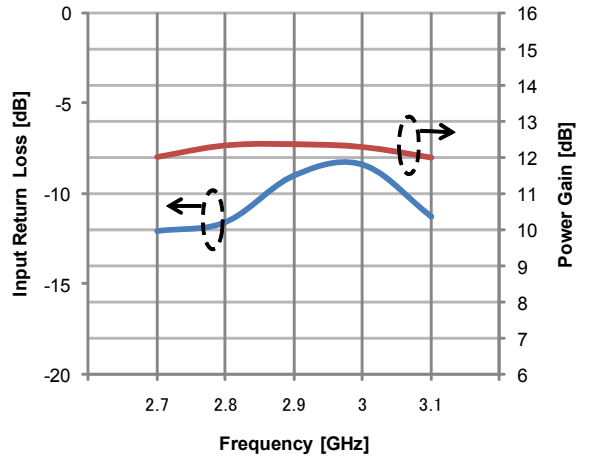
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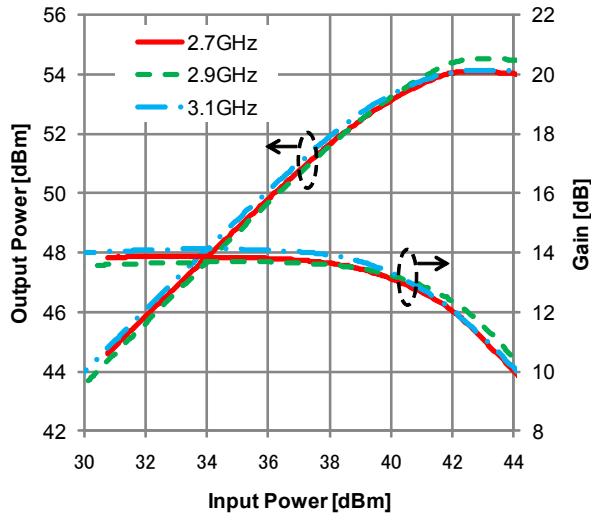
$V_{DS}=50V$, $I_{DS(DC)}=1A$, $P_{in}=15.8W$,
 $PW=200\mu\text{sec}$, Duty 10%

Figure 3. Output Power and Drain Efficiency vs Frequency



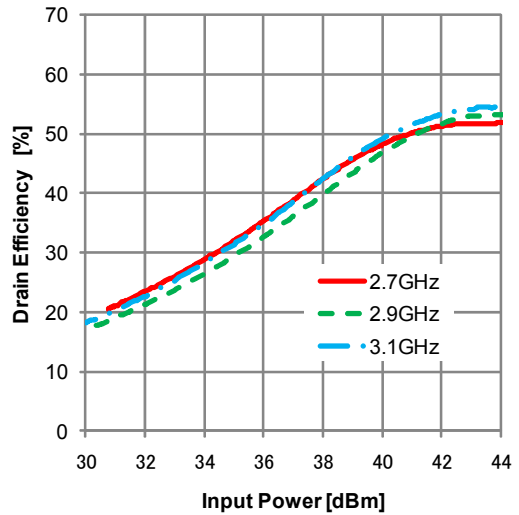
$V_{DS}=50V$, $I_{DS(DC)}=1A$, $P_{in}=15.8W$,
 $PW=200\mu\text{sec}$, Duty 10%

Figure 4. Input Return Loss and Power Gain vs Frequency



$V_{DS}=50V$, $I_{DS(DC)}=1A$,
 $PW=200\mu\text{sec}$, Duty 10%

Figure 5. Output Power and Gain vs Input Power



$V_{DS}=50V$, $I_{DS(DC)}=1A$,
 $PW=200\mu\text{sec}$, Duty 10%

Figure 6. Drain Efficiency vs Input Power



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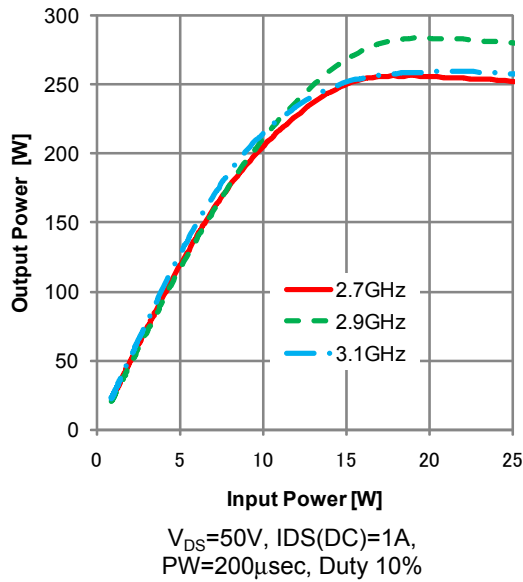


Figure 7. Output Power vs Input Power

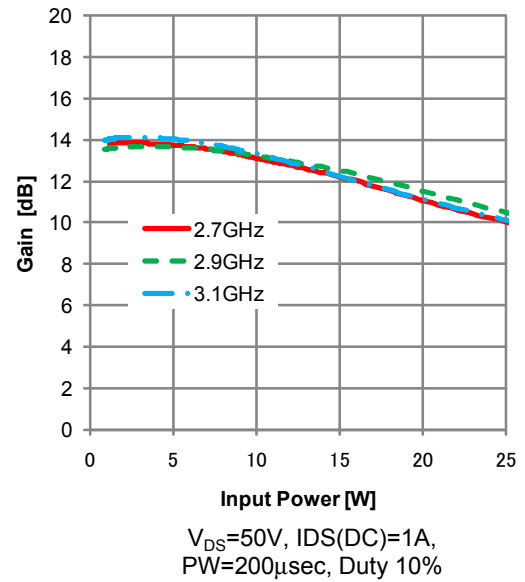


Figure 8. Gain vs Input Power

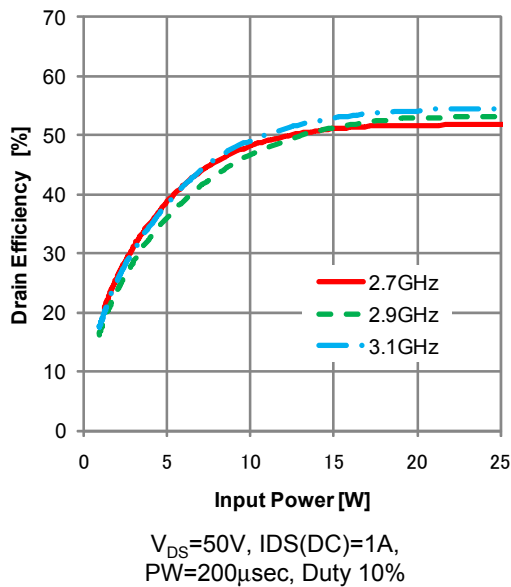


Figure 9. Drain Efficiency vs Input Power



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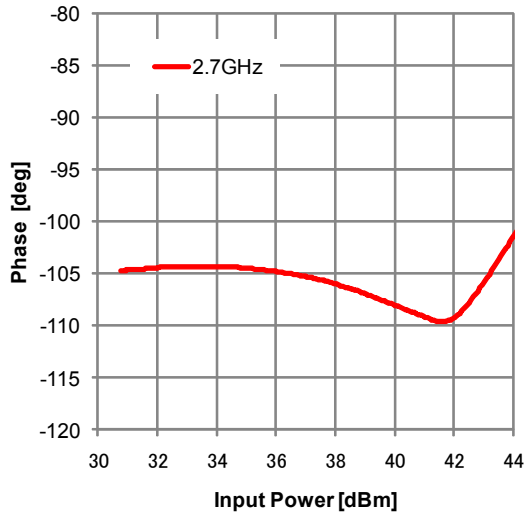


Figure 10. a) f=2.7GHz

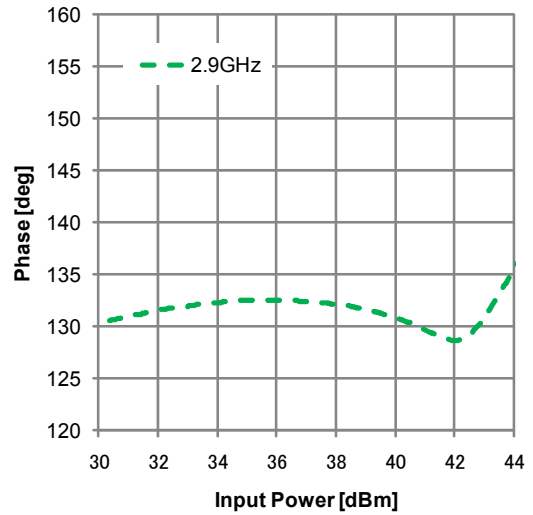


Figure 10. b) f=2.9GHz

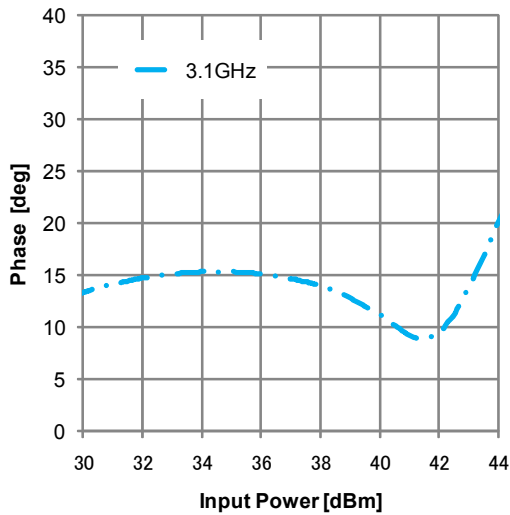


Figure 10. c) f=3.1GHz

$V_{DS}=50V$, $I_{DS}(DC)=1A$,
 $PW=200\mu sec$, Duty 10%

Figure 10. Insertion Phase shift vs Input Power



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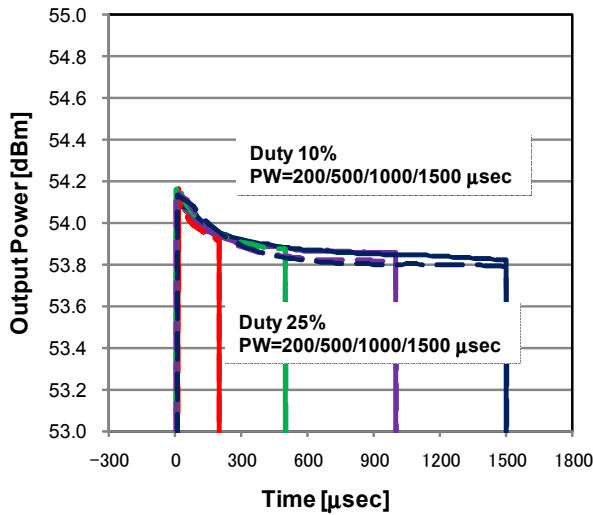


Figure 11. a) f=2.7GHz

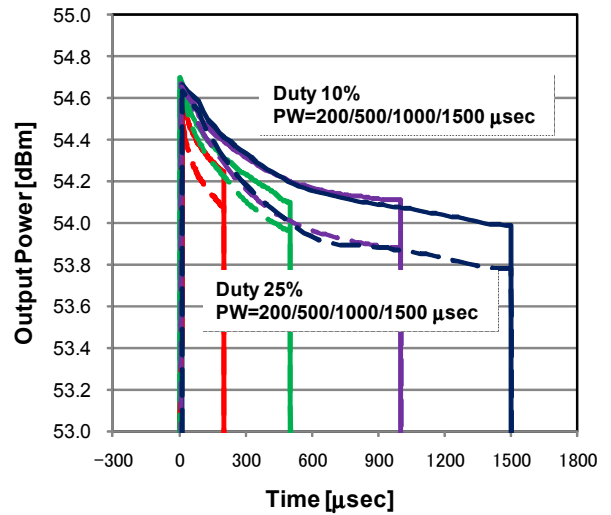


Figure 11. b) f=2.9GHz

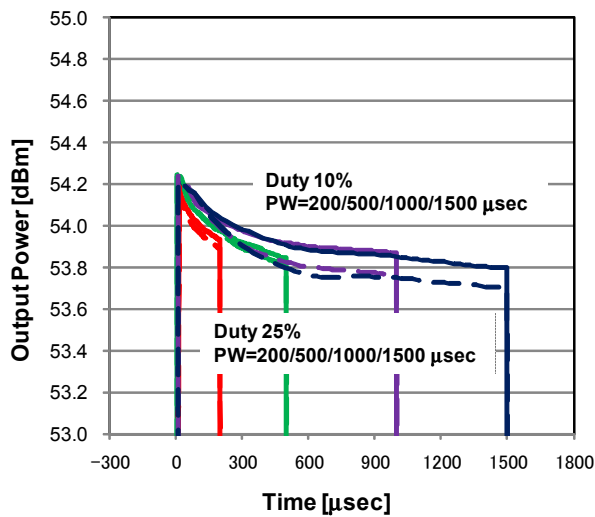


Figure 11. c) f=3.1GHz

$V_{DS}=50V, I_{DS(DC)}=1A, P_{in}=15.8W$
 PW/Duty = 200/10, 500/10, 1000/10, 1500/10,
 200/25, 500/25, 1000/25, 1500μsec/25%

Solid Line : Duty 10%
 Dashed Line : Duty 25%

Figure 11. Pulse Performance (Power) with various Pulse Condition

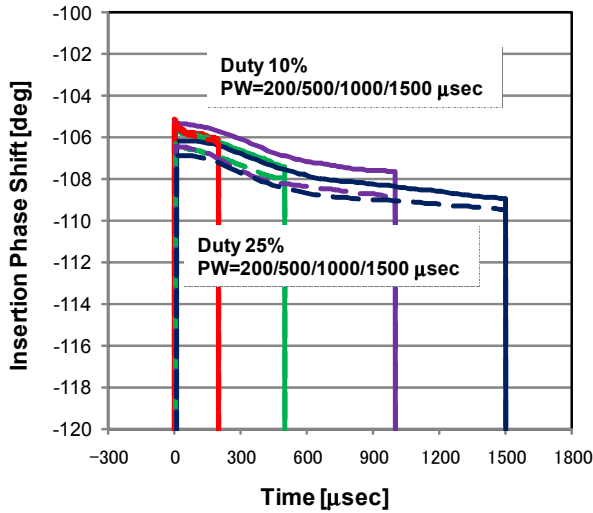


Figure 12. a) f=2.7GHz

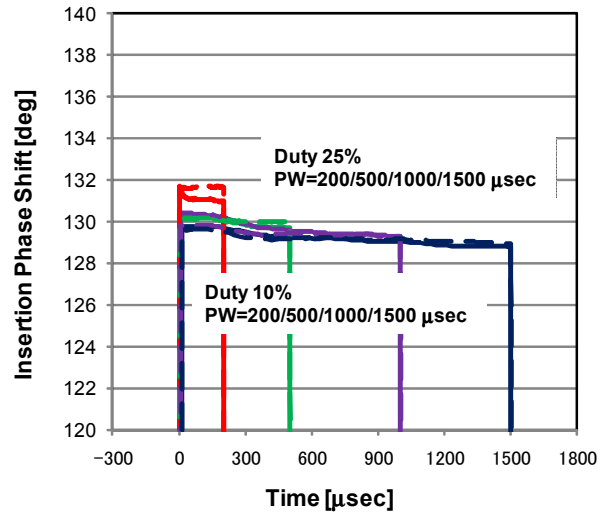


Figure 12. b) f=2.9GHz

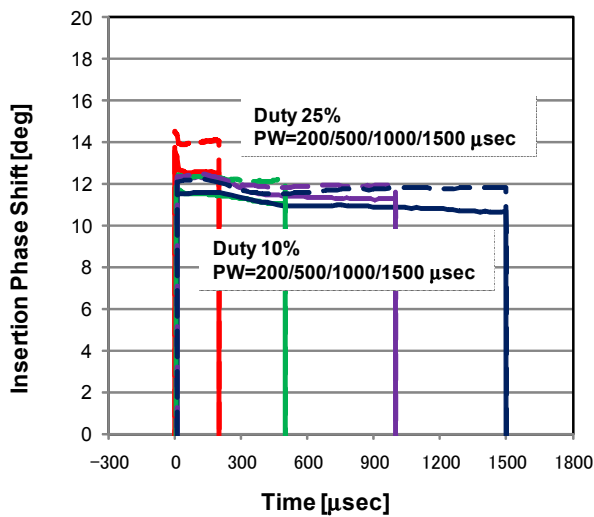


Figure 12. c) f=3.1GHz

$V_{DS}=50V, I_{DS(DC)}=1A, P_{in}=15.8W$
 PW/Duty = 200/10, 500/10, 1000/10, 1500/10,
 200/25, 500/25, 1000/25, 1500μsec/25%

Solid Line : Duty 10%
 Dashed Line : Duty 25%

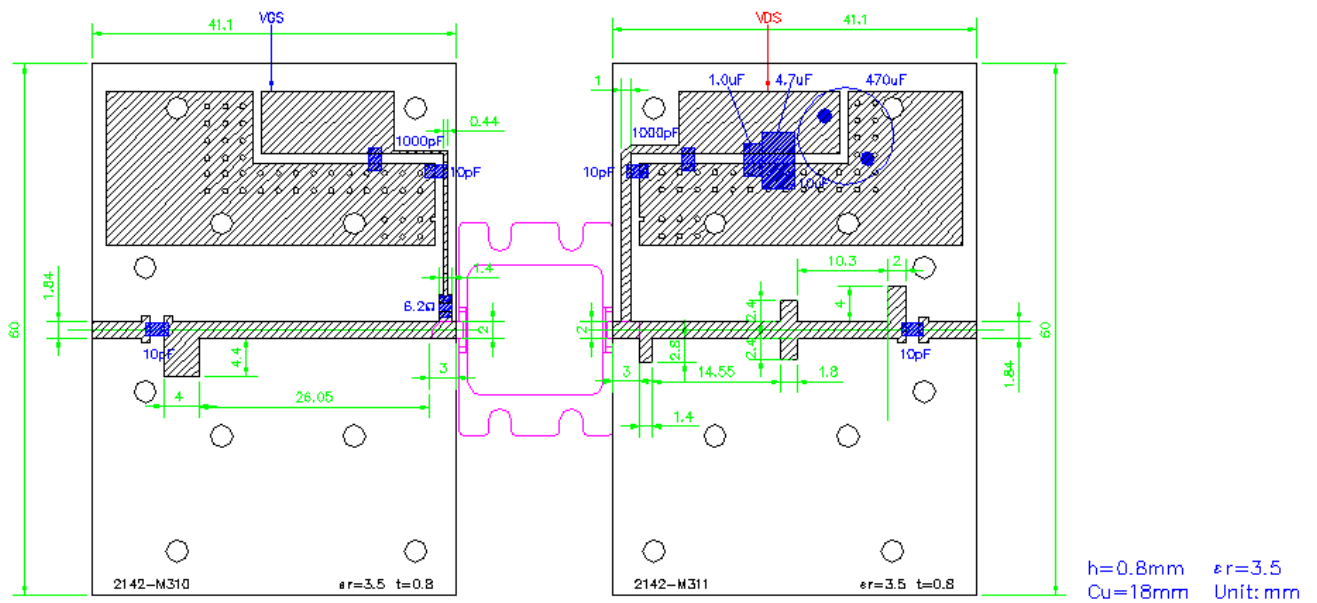
Figure 12. Pulse Performance
 (Insertion Phase Shift)
 with various Pulse Condition



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TEST FIXTURE





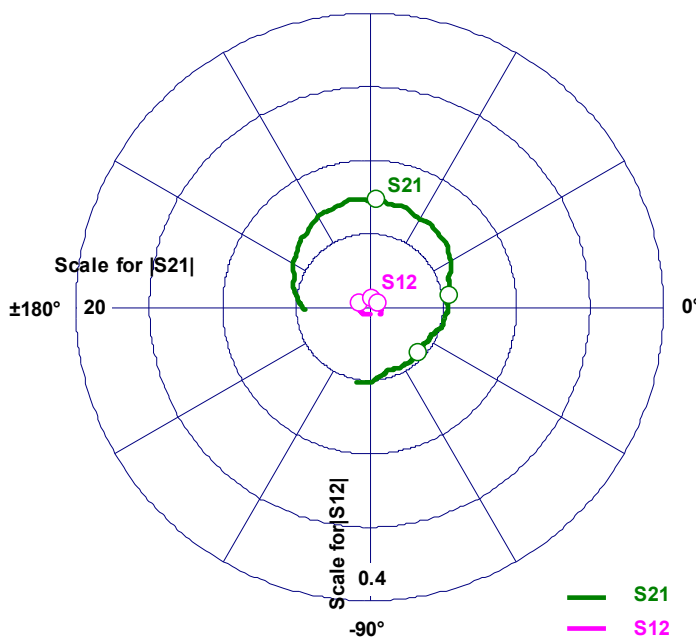
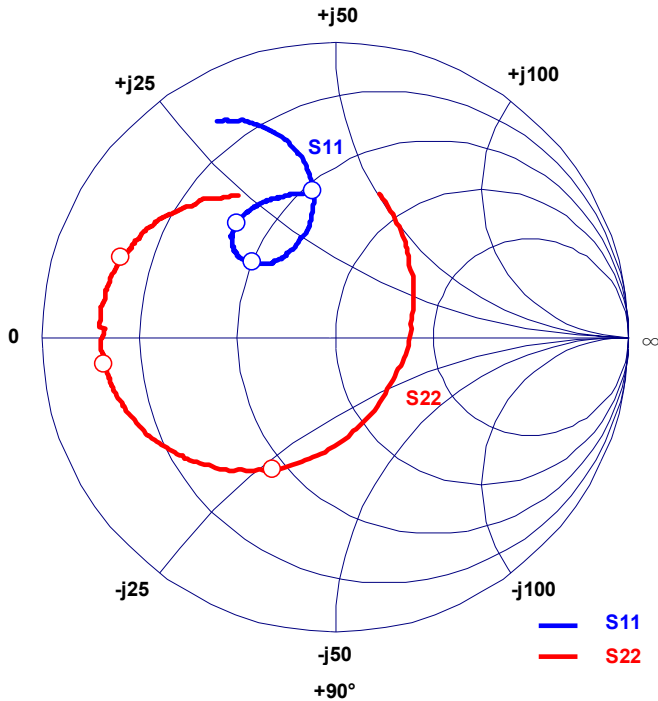
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S-parameters(1Port)

@ $V_{DS}=50V$ $I_{DS(DC)}=1A$ $f=2.5$ to $3.3GHz$
 $Z_1 = Z_s = 50ohm$ Marker: 2.7, 2.9, 3.1GHz

Freq. GHz	S11		S21		S12		S22	
	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
2.50	0.84	118.8	4.41	-177.5	0.01	-87.9	0.51	72.9
2.51	0.83	117.9	4.70	178.4	0.01	-94.5	0.48	68.7
2.52	0.83	116.9	4.90	174.4	0.01	-98.8	0.45	63.0
2.53	0.82	116.1	5.11	170.0	0.01	-102.5	0.42	56.2
2.54	0.81	115.0	5.37	165.4	0.01	-108.8	0.39	51.0
2.55	0.80	113.3	5.42	160.6	0.01	-115.4	0.35	44.5
2.56	0.79	112.5	5.66	155.9	0.01	-120.4	0.32	33.0
2.57	0.78	111.2	5.93	151.2	0.01	-126.3	0.29	23.9
2.58	0.76	110.0	6.07	146.9	0.01	-131.3	0.27	13.6
2.59	0.75	108.7	6.23	142.3	0.01	-137.1	0.25	-2.5
2.60	0.73	107.3	6.49	137.6	0.01	-143.5	0.24	-17.0
2.61	0.72	106.3	6.60	133.0	0.01	-148.7	0.24	-29.4
2.62	0.70	104.8	6.73	127.8	0.01	-156.3	0.25	-44.3
2.63	0.68	103.5	6.99	122.5	0.01	-160.5	0.28	-58.4
2.64	0.65	102.3	7.15	117.2	0.01	-166.2	0.30	-70.1
2.65	0.63	101.1	7.11	111.8	0.01	-172.1	0.33	-79.6
2.66	0.60	100.2	7.25	106.2	0.01	-177.2	0.37	-90.1
2.67	0.58	99.5	7.41	100.8	0.01	-176.1	0.40	-97.1
2.68	0.55	99.0	7.36	95.7	0.01	-171.3	0.43	-103.6
2.69	0.53	98.6	7.28	90.9	0.01	-166.6	0.47	-110.3
2.70	0.50	98.8	7.33	86.0	0.01	-160.5	0.50	-115.6
2.71	0.48	98.9	7.23	81.5	0.01	-154.1	0.52	-120.3
2.72	0.45	99.4	7.14	76.8	0.01	-147.3	0.55	-125.3
2.73	0.43	100.6	7.20	72.3	0.01	-143.0	0.58	-129.6
2.74	0.41	101.9	7.15	67.6	0.01	-136.7	0.61	-133.6
2.75	0.39	103.1	6.95	63.3	0.01	-132.7	0.63	-137.0
2.76	0.37	105.7	6.94	59.0	0.01	-128.4	0.65	-140.8
2.77	0.36	109.2	7.00	54.6	0.01	-122.8	0.67	-143.7
2.78	0.34	111.6	6.93	50.6	0.01	-118.1	0.69	-147.0
2.79	0.33	114.4	6.81	46.0	0.01	-113.8	0.70	-149.9
2.80	0.33	118.0	6.82	41.6	0.01	-109.5	0.72	-152.5
2.81	0.33	120.5	6.65	36.8	0.01	-104.5	0.73	-155.1
2.82	0.32	123.0	6.42	32.4	0.01	-100.4	0.74	-157.5
2.83	0.33	126.2	6.29	28.2	0.01	-96.9	0.75	-159.7
2.84	0.33	128.8	6.09	24.5	0.01	-92.4	0.76	-162.0
2.85	0.33	130.7	5.80	21.5	0.01	-89.5	0.76	-163.9
2.86	0.34	133.0	5.70	18.8	0.01	-86.2	0.77	-166.0
2.87	0.35	135.0	5.67	16.1	0.01	-82.9	0.78	-168.0
2.88	0.36	136.4	5.58	13.5	0.01	-78.8	0.78	-169.9
2.89	0.37	137.5	5.47	10.9	0.01	-75.1	0.79	-171.7
2.90	0.38	138.4	5.47	8.1	0.01	-72.6	0.79	-173.2
2.91	0.39	139.1	5.37	5.3	0.01	-69.0	0.79	-174.7
2.92	0.39	139.7	5.28	2.5	0.01	-66.1	0.79	-176.1
2.93	0.41	139.9	5.32	-0.4	0.01	-63.7	0.80	-177.4
2.94	0.42	140.2	5.29	-3.6	0.01	-59.9	0.80	-179.2
2.95	0.42	140.4	5.17	-7.3	0.01	-57.2	0.79	-179.3
2.96	0.43	140.3	5.14	-10.9	0.01	-54.2	0.81	-177.6
2.97	0.45	139.6	5.12	-14.3	0.01	-51.4	0.80	-176.1
2.98	0.45	139.5	4.97	-17.0	0.01	-47.7	0.80	-175.1
2.99	0.46	139.1	4.81	-19.6	0.01	-45.2	0.80	-173.6
3.00	0.47	138.5	4.76	-21.5	0.01	-43.0	0.80	-172.5
3.01	0.47	138.2	4.65	-23.4	0.01	-41.0	0.80	-171.2
3.02	0.48	137.8	4.59	-26.0	0.01	-38.3	0.80	-170.0
3.03	0.48	137.0	4.60	-28.3	0.01	-35.0	0.80	-168.6
3.04	0.49	136.3	4.58	-30.8	0.01	-32.3	0.79	-167.2
3.05	0.49	135.9	4.46	-33.2	0.01	-30.5	0.79	-165.9
3.06	0.50	134.8	4.44	-35.4	0.01	-27.9	0.79	-164.7
3.07	0.50	133.6	4.50	-37.2	0.01	-26.0	0.79	-163.8
3.08	0.51	132.6	4.47	-39.2	0.01	-24.2	0.78	-162.4
3.09	0.51	131.9	4.46	-41.2	0.01	-21.5	0.78	-161.1
3.10	0.51	130.8	4.53	-43.4	0.01	-19.3	0.78	-159.9
3.11	0.51	130.0	4.54	-45.9	0.01	-16.3	0.77	-158.2
3.12	0.51	129.2	4.52	-48.8	0.01	-13.8	0.76	-156.9
3.13	0.52	127.9	4.60	-51.6	0.01	-12.2	0.76	-155.6
3.14	0.52	126.8	4.63	-54.5	0.01	-9.2	0.75	-154.4
3.15	0.52	125.9	4.56	-57.7	0.01	-6.3	0.75	-153.1
3.16	0.52	124.5	4.58	-60.7	0.01	-4.3	0.75	-151.7
3.17	0.52	123.1	4.63	-63.4	0.01	-1.8	0.74	-150.1
3.18	0.52	121.9	4.59	-66.4	0.01	-1.2	0.73	-148.5
3.19	0.52	120.8	4.51	-68.8	0.01	-3.6	0.72	-146.7
3.20	0.52	119.2	4.52	-70.9	0.01	-5.7	0.71	-145.1
3.21	0.52	118.0	4.49	-72.8	0.01	-8.1	0.70	-143.4
3.22	0.52	116.7	4.46	-74.5	0.02	-12.0	0.69	-141.8
3.23	0.52	115.0	4.58	-76.4	0.02	-13.9	0.68	-140.0
3.24	0.51	113.3	4.70	-78.7	0.02	-16.2	0.67	-138.1
3.25	0.51	112.1	4.75	-81.5	0.02	-18.9	0.65	-136.1
3.26	0.51	110.4	4.90	-84.7	0.02	-20.2	0.65	-133.9
3.27	0.51	108.2	5.08	-88.2	0.02	-24.6	0.63	-131.8
3.28	0.51	106.6	5.14	-92.1	0.02	-27.7	0.61	-129.6
3.29	0.50	104.8	5.16	-96.2	0.02	-31.1	0.60	-127.1
3.30	0.50	102.7	5.19	-100.0	0.02	-35.6	0.58	-124.8

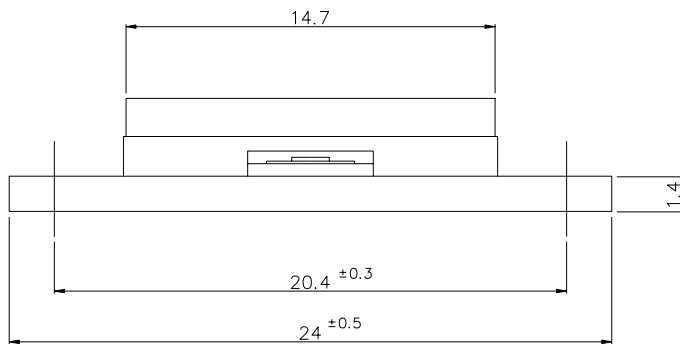
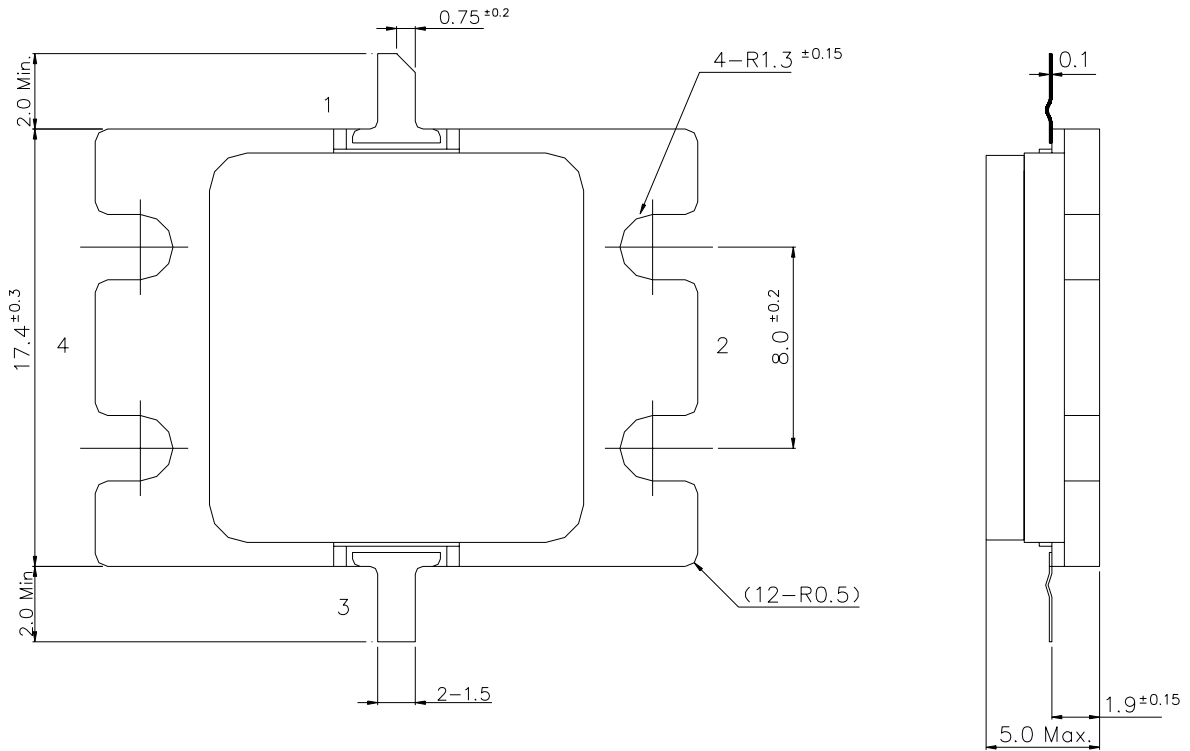




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IV Package Outline Metal-Ceramic Hermetic Package



- 1 : Gate
 - 2 : Source(Flange)
 - 3 : Drain
 - 4 : Source(Flange)
- Unit : mm



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High Voltage - High Power GaN-HEMT for Radar

For further information please contact:

<http://global-sei.com/Electro-optic/about/office.html>

CAUTION

Sumitomo Electric Device Innovations, Inc. products contain **gallium arsenide (GaAs)** which can be hazardous to the human body and the environment. For safety, observe the following procedures:

- Do not put these products into the mouth.
- Do not alter the form of this product into a gas, powder, or liquid through burning, crushing, or chemical processing as these by-products are dangerous to the human body if inhaled, ingested, or swallowed.
- Observe government laws and company regulations when discarding this product. This product must be discarded in accordance with methods specified by applicable hazardous waste procedures.